MSKSEMI















ESD

TVS

TSS

MOV

GDT

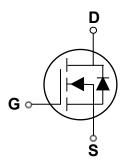
PLED

Broduct data sheet





SOT-23-3L



Features

- 30V,4.0A , RDS(ON)=42mΩ@VGS=10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

Applications

- MB / VGA / Vcore
- Load Switch
- Hand-Held Instrument

BVDSS	RDSON	ID
30V	42mΩ	4.0A

Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±12	V
L	Drain Current – Continuous (T _A =250)	4.0	А
Drain Current – C	Drain Current – Continuous (T _A =70C)	2.5	А
Ірм	Drain Current – Pulsed ¹	16	А
D-	Power Dissipation (T _A =250)	278	mW
P _D	Power Dissipation – Derate above 250	2.22	mW/ C
Гѕтс	Storage Temperature Range	-50 to 150	С
TJ	Operating Junction Temperature Range	-50 to 150	С

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
Reja	Thermal Resistance Junction to ambient		450	c/ W



Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	Vgs=0V , Ip=250uA	30			V
△BV _{DSS} /△T _J	BV _{DSS} Temperature Coefficient	Reference to 250 , ID=1mA		0.018		V/ C
	Dunin Course Legland Current	V _{DS} =30V , V _{GS} =0V , T _J =250			1	uA
I _{DSS} Drain-Source Leakage Current		V _{DS} =24V , V _{GS} =0V , T _J =1250			10	uA
Igss	Gate-Source Leakage Current	Vgs= ±12V , Vps=0V			±100	nA

On Characteristics

Decrees	RDS(ON) Static Drain-Source On-Resistance	V _{GS} =10V , I _D =4A		42	55	mΩ
RDS(ON)		V _{GS} =4.5V , I _D =3A		48	65	mΩ
V _{GS(th)}	Gate Threshold Voltage	V V 1 050		1.0	2.5	V
$\triangle V$ GS(th)	V _{GS(th)} Temperature Coefficient	Vgs=Vds , Id =250uA		-3.2		mV/ C
gfs	Forward Transconductance	V _{DS} =10V , I _D =2A		2.3		S

Dynamic and switching Characteristics

Qg	Total Gate Charge ^{2,3}		 3.1	
Qgs	Gate-Source Charge ^{2, 3}	V _{DS} =24V , V _{GS} =10V , I _D =1A	 0.1	 nC
Qgd	Gate-Drain Charge ^{2, 3}		 1.7	
T _d (on)	Turn-On Delay Time ^{2,3}		 2.2	
Tr	Rise Time ^{2,3}	V _{DD} =24V , V _{GS} =10V , R _G =3.3Ω	 6.9	
T _{d(off)}	Turn-Off Delay Time ^{2,3}	I _D =1A	 15.2	 ns
Tf	Fall Time ^{2,3}		 4.5	
Ciss	Input Capacitance		 245	
Coss	Output Capacitance	V _{DS} =25V , V _{GS} =0V , F=1MHz	 40	 pF
Crss	Reverse Transfer Capacitance		 78	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current	\/\/0\/			4.0	Α
Іѕм	Pulsed Source Current	V _G =V _D =0V , Force Current			8.0	Α
VsD	Diode Forward Voltage	Vgs=0V , Is=1A , TJ=250		-	1.2	V

- Note :

 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.

 The total deviated by pulsed pulse width < 300us . duty cycle ≤ 2%.
- The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$.
- Essentially independent of operating temperature.

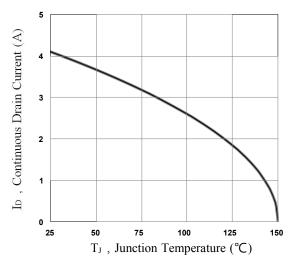


Fig. 1 Continuous Drain Current vs. TJ

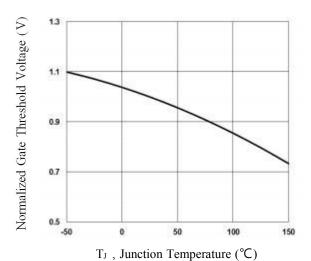


Fig. 3 Normalized V_{th} vs. T_J

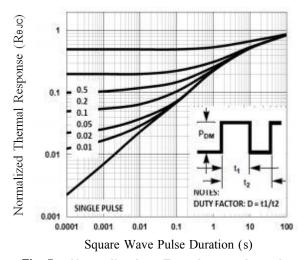


Fig. 5 Normalized Transient Impedance

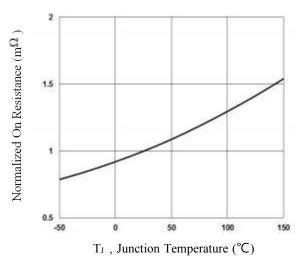


Fig. 2 Normalized RDSON vs. T.

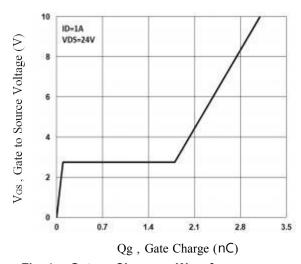
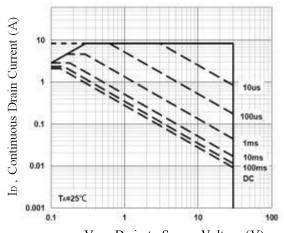


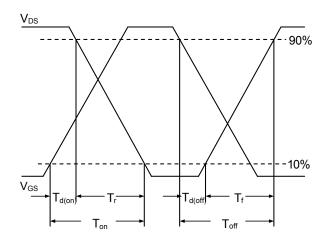
Fig. 4 Gate Charge Waveform



 $V_{DS}\,,$ Drain to Source Voltage (V)

Fig. 6 Maximum Safe Operation Area





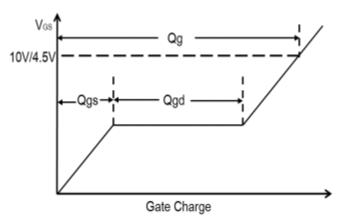


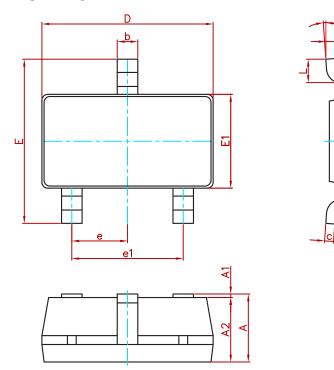
Fig. 7 Switching Time Waveform

Fig. 8 Gate Charge Waveform



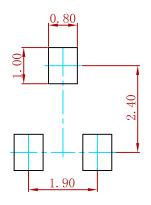
0.200

PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimete		Dimension	s In Inches
Symbol	Min.	Max.	Min.	Max.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
Е	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037((BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
AO3434A	SOT-23-3L	3000



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